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Supporting Information

Low-temperature fabrication of solution-processed HfOx gate insulator using thermally purified solution process

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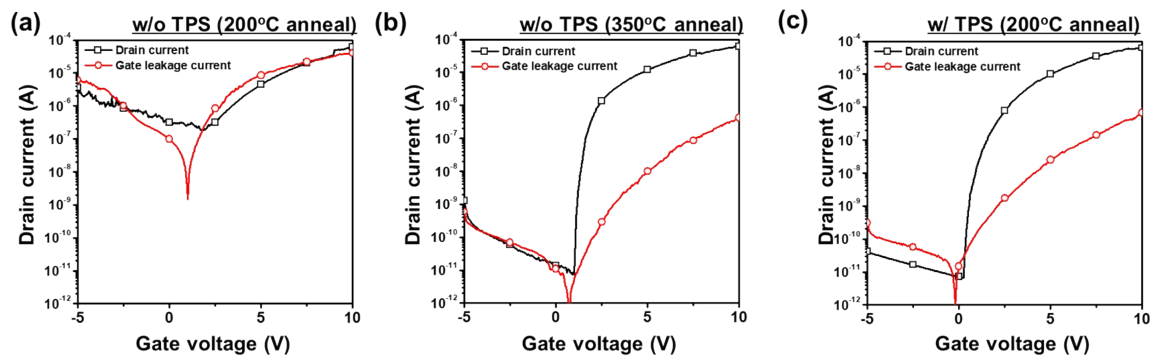

Figure S1. Gate leakage current of In_2O_3 TFT with HfO_x without TPS annealed at (a) 200°C, (b) 350°C, and (c) with TPS annealed at 200°C

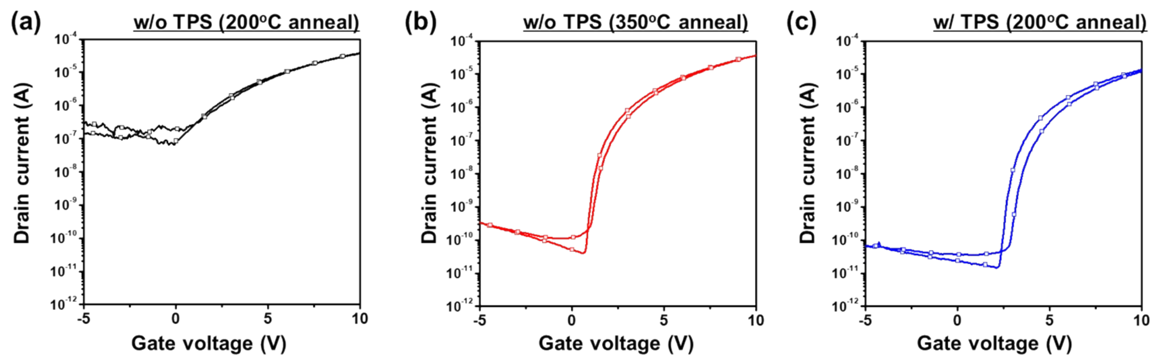

Figure S2. Hysteresis characteristics of In_2O_3 TFT with HfO_x without TPS annealed at (a) 200°C, (b) 350°C, and (c) with TPS annealed at 200°C

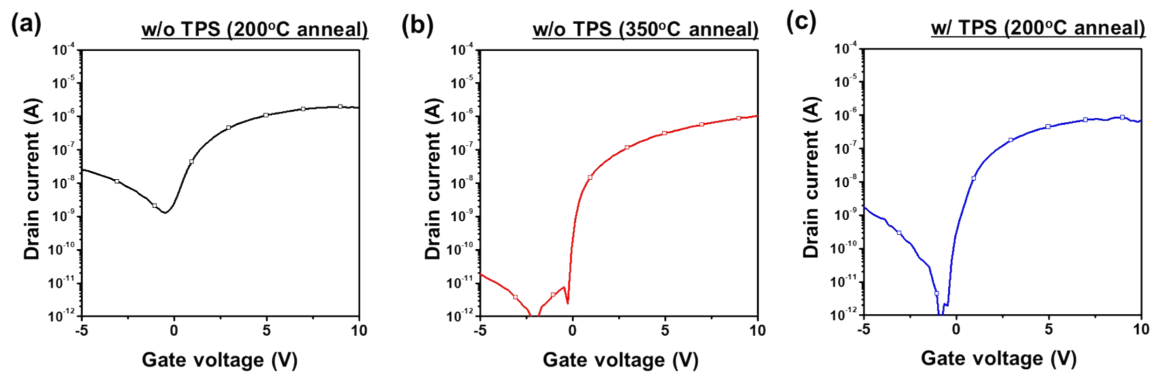

Figure S3. Transfer characteristics at linear region of In_2O_3 TFT with HfO_x without TPS annealed at (a) 200°C, (b) 350°C, and (c) with TPS annealed at 200°C

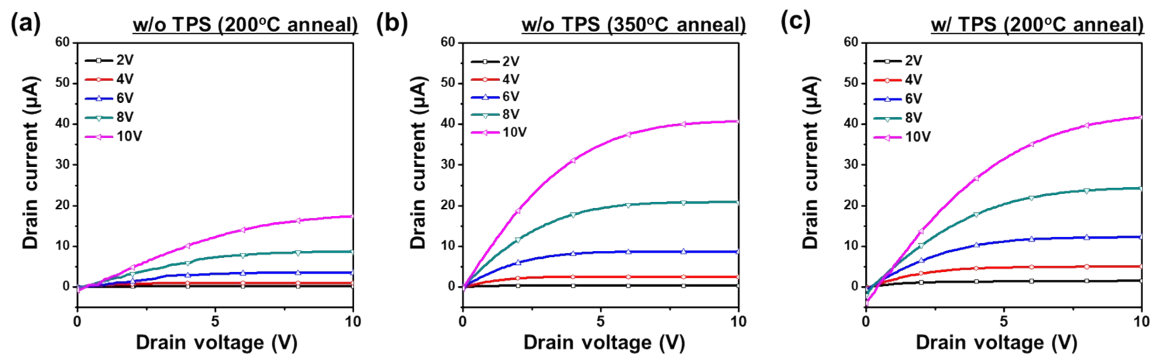

Figure S4. Output characteristics of In_2O_3 TFT with HfO_x without TPS annealed at (a) 200°C, (b) 350°C, and (c) with TPS annealed at 200°C